

Standard specifications of 100 mm β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

Items	Specifications
Dopant	Si+Cl ^{*1} (n-type)
Doping concentration (cm ⁻³)	1×10^{16}
Thickness (μm) *Selectable in 1 μm increments.	5–10

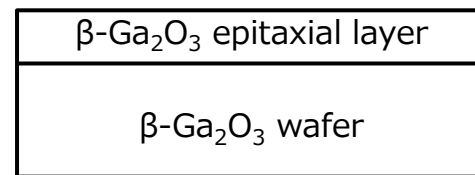
*1: Unintentionally-doped

Epi-Wafer

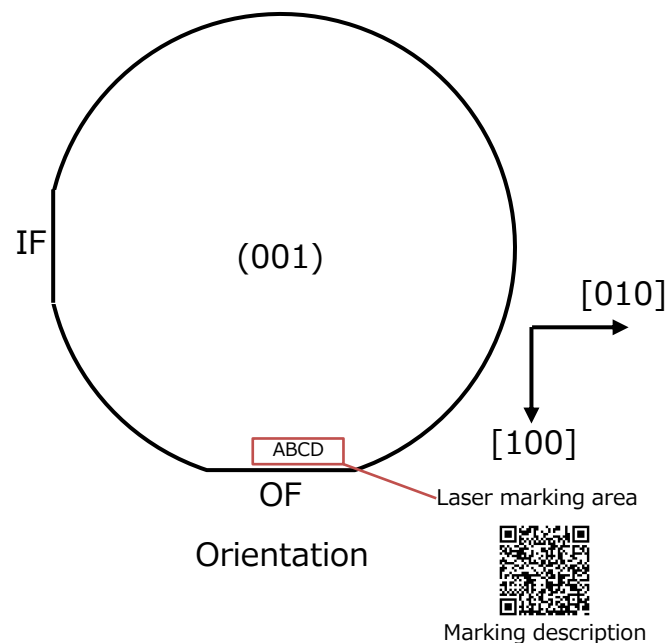
Items	Specifications
Substrate dopant	Sn (n-type)
Substrate resistivity (Ω·cm)	0.007–0.042
Surface orientation	(001)
Backside finish	CMP
Wafer thickness (μm)	650
XRD FWHM (arcsec) *Not listed on delivery inspection sheet.	≤ 50

Remarks

- 1 Chipping may be up to <18 mm on the opposite side of the OF, and <32.5 ± 2.5 mm on the OF side.
- 2 These products must be used for research and development purposes only.
- 3 The substrates must not be used as a seed crystal.
- 4 The specifications are subject to change without notice.



Cross section of β -Ga₂O₃ epitaxial wafer



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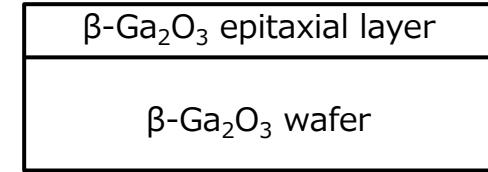
2025. 9. 29

Standard specifications of 2 inch β -Ga₂O₃ epitaxial wafer (by HVPE)

Epitaxial layer

Items	Specifications
Dopant	Si+Cl ^{*1} (n-type)
Doping concentration (cm ⁻³)	1×10^{16}
Thickness (μm) *Selectable in 1 μm increments.	5–10

*1: Unintentionally-doped



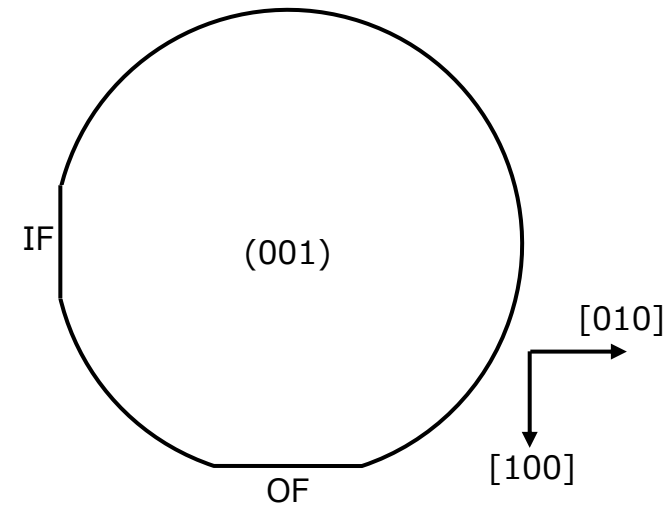
Cross section of β -Ga₂O₃ epitaxial wafer

Epi-Wafer

Items	Specifications
Substrate dopant	Sn (n-type)
Substrate resistivity ($\Omega \cdot \text{cm}$)	0.007–0.042
Surface orientation	(001)
Backside finish	CMP
Wafer thickness (μm)	650
XRD FWHM (arcsec) *Not listed on delivery inspection sheet.	≤ 50

Remarks

- 1 Chipping may be up to <8 mm on the opposite side of the OF, and $<15.9 \pm 2.5$ mm on the OF side.
- 2 These products must be used for research and development purposes only.
- 3 The substrates must not be used as a seed crystal.
- 4 The specifications are subject to change without notice.



Orientation



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